Journal of Crystal Growth 116 (1992) 532–535
North-Holland

JOURNAL OF CRYSTAL GROWTH

Author index

Adair, J.H., see Rossetti, Jr. 116 (1992) 251
Aibara, S. and Y. Morita, Crystal growth of hen egg-white lysozyme using a crystallization vessel produced for spacelab experiment 116 (1992) 289
Alexiev, D., Extraction of metallic impurity from gallium 116 (1992) 240
Appenzeller, J., see Hardtdegen 116 (1992) 521
Asano, M., see Harada 116 (1992) 243
Aseev, A.L., see Krasilnikov 116 (1992) 178
Azoulay, M., S. Rotter, G. Gafni and M. Roth, The crystalline quality distribution in CdZnTe single crystal correlated to the interface shape during growth 116 (1992) 515

Babijchuk, I.P., E.F. Dolzhenkova, M.B. Kosmyna and V.V. Nekrasov, Growth of HTSC Bi-containing single crystals by the spontaneous crystallization method 116 (1992) 529
Balzuweit, K., see Vogels 116 (1992) 397
Basmaji, P., see Notari 116 (1992) 518
Beam III, E.A., T.S. Henderson, A.C. Seabaugh and J.Y. Yang, The use of tertiarybutylphosphine and tertiarybutylarsine for the metalorganic molecular beam epitaxy of the $In_{0.53}Ga_{0.47}As/InP$ and $In_{0.48}Ga_{0.52}P/GaAs$ materials systems 116 (1992) 436
Bennema, P., see Vogels 116 (1992) 397
Bensaoula, A., see Hansen 116 (1992) 271
Binsma, J.J.M., see Kolar 116 (1992) 473
Bochkarev, A.E., see Kazakov 116 (1992) 204
Bowen, D.K., see Capano 116 (1992) 260
Bublik, V.T., see Charniy 116 (1992) 369

Capano, M.A., L. Hart, D.K. Bowen, D. Gordon-Smith, C.R. Thomas, C.J. Gibbings, M.A.G. Halliwell and L.W. Hobbs, Strain relaxation in $Si_{1-x}Ge_x$ layers on Si(001) 116 (1992) 260
Carlson, D.J. and A.F. Witt, Quantitative analysis of the effects of vertical magnetic fields on microsegregation in Te-doped LEC GaAs 116 (1992) 461
Castillo, J.L., P.L. García-Ybarra and D.E. Rosner, Morphological instability of a thermophoretically growing deposit 116 (1992) 105
Chandley, P. and R.J.H. Clark, The flux growth of single crystals of vanadium-doped $ZrSiO_4$, $HfSiO_4$, $ZrGeO_4$ and $HfGeO_4$ as well as of chromium-doped $ZrSiO_4$ and terbium-doped $ZrGeO_4$ 116 (1992) 151
Charniy, L.A., A.N. Morozov, K.D. Scherbachov, V.T. Bublik and I.V. Stepantsova, X-ray diffuse scattering identification of matrix As-rich microdefects in GaAs crystals 116 (1992) 369
Clark, R.J.H., see Chandley 116 (1992) 151
Cot, L., see Gómez Morales 116 (1992) 427
Cuisinier, F.J.G., J.C. Voegel, J. Yacaman and R.M. Frank, Structure of initial crystals formed during human amelogenesis 116 (1992) 314

Dassonville, R., see Kern 116 (1992) 191
De Croon, M.H.J.M., see Hageman 116 (1992) 169
Dolginov, L.M., see Kazakov 116 (1992) 204
Dolzhenkova, E.F., see Babijchuk 116 (1992) 529
Durand, J., see Gómez Morales 116 (1992) 427
Dutta, P.K., see Narlikar 116 (1992) 37

Fawcett, P.N., B.A. Joyce, X. Zhang and D.W. Pashley, Interface structure of InAs grown on GaAs(001) surfaces by molecular beam epitaxy 116 (1992) 81
Fernandez, R., RHEED oscillations of arsenic-controlled growth conditions to optimize MBE growth of III/V heterostructures 116 (1992) 98
Frank, R.M., see Cuisinier 116 (1992) 314

Gafni, G., see Azoulay 116 (1992) 515
Gao, Y., see Kazmierski 116 (1992) 75
García-Ybarra, P.L., see Castillo 116 (1992) 105
Ge, Y.L., see Jin 116 (1992) 524
Gibbings, C.J., see Capano 116 (1992) 260
Giling, L.J., see Hageman 116 (1992) 169
Ginde, R.M. and A.S. Myerson, Cluster size estimation in binary supersaturated solutions 116 (1992) 41
Gómez Morales, J., R. Rodríguez Clemente, J. Durand and L. Cot, Solubility of berlinite in H_2SO_4–HCl mixtures under hydrothermal conditions 116 (1992) 427
Gordon-Smith, D., see Capano 116 (1992) 260

Grásza, K. and U. Zuzga-Grasza, Temperature field computations in $Pb_{1-x}Sn_xTe$ crystal grown by inverted Bridgman method 116 (1992) 139
Guan, Q.C., see Wang 116 (1992) 27
Gupta, M.K., see Narlikar 116 (1992) 37

Hageman, P.R., M.H.J.M. de Croon, J.N.H. Reek and L.J. Giling, Pressure and temperature dependence of silicon doping of GaAs using Si_2H_6 in metalorganic chemical vapour deposition 116 (1992) 169
Halliwell, M.A.G., see Capano 116 (1992) 260
Hansen, H.S., A. Bensaoula, S. Tougaard, J. Zborowski and A. Ignatiev, The temperature dependent variation of bulk and surface composition of $In_xGa_{1-x}As$ on GaAs grown by chemical beam epitaxy studied by RHEED, X-ray diffraction and XPS 116 (1992) 271
Harada, T., M. Asano and Y. Mizutani, Epitaxial growth of Ag deposited on air-cleaved MgO(100) surface by molecular beam deposition 116 (1992) 243
Hardtdegen, H., R. Meyer, H. Løken-Larsen, J. Appenzeller, Th. Schäpers and H. Lüth, Extremely high electron mobilities in modulation doped $Ga_{1-x}In_xAs/InP$ heterostructures grown by LP-MOVPE 116 (1992) 521
Hart, L., see Capano 116 (1992) 260
Hayashi, T., see Kitamura 116 (1992) 327
Henderson, T.S., see Beam III 116 (1992) 436
Hipólito, O., see Notari 116 (1992) 518
Hobbs, L.W., see Capano 116 (1992) 260
Hosogai, H., see Sakai 116 (1992) 421
Hu, Z.Q., see Jin 116 (1992) 524

Igasaki, Y., Epitaxial growth of aluminum-doped zinc oxide films on $(11\bar{2}0)$ oriented sapphire substrates 116 (1992) 357
Ignatiev, A., see Hansen 116 (1992) 271
Iijima, M., H. Tohda and Y. Moriwaki, Growth and structure of lamellar mixed crystals of octacalcium phosphate and apatite in a model system of enamel formation 116 (1992) 319
Ishigaki, T., see Okada 116 (1992) 307
Ishikawa, T., see Kimura 116 (1992) 22
Iyi, N., see Kitamura 116 (1992) 327

Jiang, S.S., Q. Li and X.Y. Xu, Growth defects of natural beryls observed by X-ray topography 116 (1992) 93
Jin, H., Y.L. Ge, Q.M. Liu, Z.Q. Hu and C.H. Shi, Morphologies and structures of Bi-based oxide fibrous crystals 116 (1992) 524
Joyce, B.A., see Fawcett 116 (1992) 81

Karl, N., see Möbus 116 (1992) 495
Kawakita, T., see Sakai 116 (1992) 421
Kazakov, A.I., I.N. Kishmar, A.E. Bochkarev and L.M. Dolginov, Stability analysis of quaternary $In_xGa_{1-x}Sb_yAs_{1-y}$ alloys 116 (1992) 204
Kazmierski, C., D. Robein and Y. Gao, Universal iron behaviour in Zn-, Cd- and Be-doped p-type InP 116 (1992) 75
Kelly, K.W., see Motakef 116 (1992) 242
Kern, R. and R. Dassonville, Growth inhibitors and promoters examplified on solution growth of paraffin crystals 116 (1992) 191
Kimura, R., M. Konagai and K. Takahashi, Atomic layer epitaxy of ZnSe on GaAs(100) by metalorganic molecular beam epitaxy 116 (1992) 283
Kimura, S., T. Ishikawa, J. Mizuki and J. Matsui, Analysis of minute strain fields around A-swirl defects in a float zone silicon crystal by means of plane wave X-ray topography using extremely collimated X-rays 116 (1992) 22
Kimura, S., see Kitamura 116 (1992) 327
Kishmar, I.N., see Kazakov 116 (1992) 204
Kitamura, K., J.K. Yamamoto, N. Iyi, S. Kimura and T. Hayashi, Stoichiometric $LiNbO_3$ single crystal growth by double crucible Czochralski method using automatic powder supply system 116 (1992) 327
Koai, K., see Motakef 116 (1992) 242
Kobayashi, T., see Möbus 116 (1992) 495
Kolar, Z.I., J.J.M. Binsma and B. Subotić, Kinetic study of the solution-mediated transformation of orthorhombic barium fluoride into cubic barium fluoride 116 (1992) 473
Komatsu, S., see Okada 116 (1992) 307
Konagai, M., see Kimura 116 (1992) 283
Kosmyna, M.B., see Babijchuk 116 (1992) 529
Krasilnikov, A.B., A.V. Latyshev, A.L. Aseev and S.I. Stenin, Monoatomic step clustering during superstructural transitions on Si(111) surface 116 (1992) 178
Kurlov, V.N., see Rossolenko 116 (1992) 185

Lang, A.R., see Walmsley 116 (1992) 225
Latyshev, A.V., see Krasilnikov 116 (1992) 178
Li, Q., see Jiang 116 (1992) 93
Lin, C.H., see Wang 116 (1992) 483
Liu, Q.M., see Jin 116 (1992) 524
Liu, Y.G., see Wang 116 (1992) 27
Løken-Larsen, H., see Hardtdegen 116 (1992) 521
Łukasiewicz, T. and A. Majchrowski, Czochralski growth of TeO_2 single crystals under conditions of forced convection in the melt 116 (1992) 364
Lumley, J.L., see Ristorcelli 116 (1992) 447
Luo, Zundu, see Wang 116 (1992) 505

Lüth, H., see Tang 116 (1992) 1
Lüth, H., see Hardtdegen 116 (1992) 521

Majchrowski, A., see Łukasiewicz 116 (1992) 364
Matsui, J., see Kimura 116 (1992) 22
Matsumoto, S., see Okada 116 (1992) 307
McKee, R.A., see Walker 116 (1992) 235
Meekes, H., see Vogels 116 (1992) 397
Meyer, R., see Hardtdegen 116 (1992) 521
Migita, M., see Ohsawa 116 (1992) 351
Mizuki, J., see Kimura 116 (1992) 22
Mizutani, Y., see Harada 116 (1992) 243
Möbus, M., N. Karl and T. Kobayashi, Structure of perylene-tetracarboxylic-dianhydride thin films on alkali halide crystal substrates 116 (1992) 495
Morita, Y., see Aibara 116 (1992) 289
Moriwaki, Y., see Iijima 116 (1992) 319
Moriyoshi, Y., see Okada 116 (1992) 307
Morozov, A.N., see Charniy 116 (1992) 369
Motakef, S., K.W. Kelly and K. Koai, Comparison of calculated and measured dislocation density in LEC-grown GaAs crystals (E) 116 (1992) 242
Myerson, A.S., see Ginde 116 (1992) 41

Narlikar, A.V., P.K. Dutta, S.B. Samanta, O.N. Srivastava, P. Ramasamy, S.C. Sabarwal, M.K. Gupta and B.D. Padalia, STM studies of growth spirals in bulk single crystals of superconducting Y-123 and Bi-2122 116 (1992) 37
Nekrasov, V.V., see Babijchuk 116 (1992) 529
Newnham, R.E., see Rossetti, Jr. 116 (1992) 251
Notari, A.C., B. Schrappe, P. Basmaji and O. Hipólito, Heavily Se spike-doped GaAs grown by molecular beam epitaxy 116 (1992) 518

Ogihara, S., see Yase 116 (1992) 333
Ohsawa, J., A. Tomita and M. Migita, LPE growth of undoped n-type GaAs at 636°C with extremely low compensation 116 (1992) 351
Okada, K., S. Komatsu, T. Ishigaki, S. Matsumoto and Y. Moriyoshi, Spontaneous growth of whiskers from an interlayer of Mo_2C beneath a diamond particle deposited in a combustion-flame 116 (1992) 307
Okada, M., see Yase 116 (1992) 333
Olszyna, A., see Sokołowska 116 (1992) 507
Onuma, K., see Sakai 116 (1992) 421
Ovrutsky, A.M., Numerical analysis of faceted shape stability during growth from stagnant solutions 116 (1992) 158

Padalia, B.D., see Narlikar 116 (1992) 37
Parsons, J.D., Inverted-vertical OMVPE reactor: design and characterization 116 (1992) 387
Pashley, D.W., see Fawcett 116 (1992) 81
Patel, H. and M.E. Pemble, External reflection IR spectroscopy from trimethylgallium adsorbed at a GaAs(100) surface at 300 K – a feasibility study 116 (1992) 511
Pemble, M.E., see Patel 116 (1992) 511
Pet'kov, I.S., see Rossolenko 116 (1992) 185

Radhakrishnan, S. and J.M. Schultz, Polymer-induced crystallization of inorganic salts: PEO–$CuCl_2$ 116 (1992) 378
Ramasamy, P., see Narlikar 116 (1992) 37
Rashkovich, L.N., see Shekunov 116 (1992) 340
Red'kin, B.S., see Rossolenko 116 (1992) 185
Reek, J.N.H., see Hageman 116 (1992) 169
Rinaudo, C. and A. Zarka, X-ray topographic study of synthetic single and twinned gypsum crystals 116 (1992) 87
Ristorcelli, J.R. and J.L. Lumley, Instabilities, transition and turbulence in the Czochralski crystal melt 116 (1992) 447
Rivas, D., J. Sanz and C. Vázquez, Temperature field in a cylindrical crystal heated in a mono-ellipsoid mirror furnace 116 (1992) 127
Robein, D., see Kazmierski 116 (1992) 75
Rodríguez Clemente, R., see Gómez Morales 116 (1992) 427
Rodway, D.C., A simple system for multiwafer large area, thick film growth of cadmium telluride on gallium arsenide 116 (1992) 55
Rooney, M.-L.T., {115} Growth in boron-doped synthetic diamonds 116 (1992) 15
Rosner, D.E., see Castillo 116 (1992) 105
Rossetti, Jr., G.A., D.J. Watson, R.E. Newnham and J.H. Adair, Kinetics of the hydrothermal crystallization of the perovskite lead titanate 116 (1992) 251
Rossolenko, S.N., I.S. Pet'kov, V.N. Kurlov and B.S. Red'kin, Servo-controlled crystal growth by the Czochralski method estimating the state vector of the controlled object 116 (1992) 185
Roth, M., see Azoulay 116 (1992) 515
Rotter, S., see Azoulay 116 (1992) 515
Rousseau, R.W., see Tai 116 (1992) 294

Sabarwal, S.C., see Narlikar 116 (1992) 37
Sakai, H., H. Hosogai, T. Kawakita, K. Onuma and K. Tsukamoto, Transformation of α-glycine to γ-glycine 116 (1992) 421
Samanta, S.B., see Narlikar 116 (1992) 37
Sano, M., see Yase 116 (1992) 333
Sanz, J., see Rivas 116 (1992) 127
Schäpers, Th., see Hardtdegen 116 (1992) 521
Scherbachov, K.D., see Charniy 116 (1992) 369
Schrappe, B., see Notari 116 (1992) 518
Schultz, J.M., see Radhakrishnan 116 (1992) 378
Seabaugh, A.C., see Beam III 116 (1992) 436

Shekunov, B.Yu., L.N. Rashkovich and L.L. Smol'skii, Nonstationary growth of the cubic faces of a barium nitrate crystal 116 (1992) 340
Shi, C.H., see Jin 116 (1992) 524
Shih, Z.W., see Wang 116 (1992) 483
Smol'skii, L.L., see Shekunov 116 (1992) 340
Sokołowska, A. and A. Olszyna, Electron assisted chemical synthesis of E-BN 116 (1992) 507
Speckman, D.M., Ultraviolet and infrared absorption spectra of promising organo-arsine photochemical vapor deposition reagents 116 (1992) 48
Srivastava, O.N., see Narlikar 116 (1992) 37
Stenin, S.I., see Krasilnikov 116 (1992) 178
Stepantsova, I.V., see Charniy 116 (1992) 369
Subotić, B., see Kolar 116 (1992) 473
Suddath, F.L., see Wilson 116 (1992) 414

Tai, C.Y., J.F. Wu and R.W. Rousseau, Interfacial supersaturation, secondary nucleation, and crystal growth 116 (1992) 294
Takahashi, K., see Kimura 116 (1992) 283
Tang, H.P., L. Vescan and H. Lüth, Equilibrium thermodynamic analysis of the Si–Ge–Cl–H system for atmospheric and low pressure CVD of $Si_{1-x}Ge_x$ 116 (1992) 1
Thomas, C.R., see Capano 116 (1992) 260
Tohda, H., see Iijima 116 (1992) 319
Tomita, A., see Ohsawa 116 (1992) 351
Tougaard, S., see Hansen 116 (1992) 271
Tronin, A.Yu., Ellipsometric study of growing crystal face: $(10\bar{1}0)$ $LiIO_3$ 116 (1992) 63
Tsukamoto, K., see Sakai 116 (1992) 421

Vázquez, C., see Rivas 116 (1992) 127
Vescan, L., see Tang 116 (1992) 1
Voegel, J.C., see Cuisinier 116 (1992) 314
Vogels, L.J.P., K. Balzuweit, H. Meekes and P. Bennema, A study on the morphology and stability of incommensurately modulated structures; a case study of $((CH_3)_4N)_2ZnCl_{4-x}Br_x$ 116 (1992) 397

Walker, F.J. and R.A. McKee, High-temperature stability of molecular beam epitaxy-grown multilayer ceramic composites: TiO/Ti_2O_3 116 (1992) 235
Walmsley, J.C. and A.R. Lang, Study of a platelet-free infilling of a crack in natural diamond: evidence for a late growth event 116 (1992) 225
Wang, Guofu and Zundu Luo, Crystal growth of $KY(WO_4)_2:Er^{3+},Yb^{3+}$ 116 (1992) 505
Wang, J.Y., Q.C. Guan, J.Q. Wei, M. Wang and Y.G. Liu, Growth and characterization of cubic $KTa_{1-x}Nb_xO_3$ crystals 116 (1992) 27
Wang, M., see Wang 116 (1992) 27
Wang, M.L., Z.W. Shih and C.H. Lin, Kinetics of producing barium hexaferrite in a low alkaline concentration by hydrothermal method 116 (1992) 483
Wargo, M.J. and A.F. Witt, Real time thermal imaging for analysis and control of crystal growth by the Czochralski technique 116 (1992) 213
Watson, D.J., see Rossetti, Jr. 116 (1992) 251
Wei, J.Q., see Wang 116 (1992) 27
Wilson, L.J. and F.L. Suddath, Control of solvent evaporation in hen egg white lysozyme crystallization 116 (1992) 414
Witt, A.F., see Wargo 116 (1992) 213
Witt, A.F., see Carlson 116 (1992) 461
Wu, J.F., see Tai 116 (1992) 294

Xu, X.Y., see Jiang 116 (1992) 93

Yacaman, J., see Cuisinier 116 (1992) 314
Yamamoto, J.K., see Kitamura 116 (1992) 327
Yang, J.Y., see Beam 116 (1992) 436
Yase, K., S. Ogihara, M. Sano and M. Okada, Thin film formation of polymorph-controlled triglycerides by physical vapor deposition 116 (1992) 333

Zarka, A., see Rinaudo 116 (1992) 87
Zborowski, J., see Hansen 116 (1992) 271
Zhang, X., see Fawcett 116 (1992) 81
Zuzga-Grasza, U., see Grasza 116 (1992) 139

Journal of Crystal Growth 116 (1992) 536–538
North-Holland

JOURNAL OF CRYSTAL GROWTH

Subject index

Adsorption 511
Aluminum
– gallium arsenide 98
– orthophosphate 427
Apparatus
– for solution growth
– – solvent evaporation
– – – of lysozyme 414
– for thin film growth
– – by metalorganic molecular beam epitaxy
– – – of zinc selenide 283
– for miscellaneous purposes
– – automatic powder supply system 327
– – crystal growth under microgravity 289
– – epitaxial growth (MOVPE) reactor 387
– – thermal imaging 213
– – ultrahigh vacuum evaporation 55
Arsenic
– organic 48

Barium
– fluoride 473
– hexaferrite 483
– nitrate 340
Beryl 93
Bismuth 158
– strontium calcium cuprate 37, 524, 529
Boron
– nitride 507
Boundary layer control 63

Cadmium
– telluride 55
– zinc telluride 515
Calcium
– hydroxyapatite 314, 319
– sulphate dihydrate 87
Cellular growth 364
Characterization methods
– by absorption spectroscopy 48, 327
– by Auger electron spectroscopy 213
– by differential thermal analysis 505
– by electrical methods 27, 169, 351, 387, 518, 521, 524
– by electron diffraction 495, 524
– by electron microscopy 15, 81, 225, 243, 251, 307, 314, 319, 333, 436, 495, 507, 524, 529
– by electron probe microanalysis 151, 524
– by ellipsometry 63, 387
– by Fourier transform infrared 511
– by infrared spectroscopy 15, 48, 461
– by interferometry 64, 340
– by low energy electron diffraction 243
– by optical microscopy 15, 27, 93, 158, 213, 283, 289, 378, 461, 473, 524, 529
– by particle size distribution analysis 41, 473
– by photoluminescence 169, 283, 351, 387
– by photorefraction 27
– by reflection electron microscopy 178
– by reflection high energy electron diffraction 98, 271
– by scanning tunneling microscopy 37
– by secondary ion mass spectrometry 55, 75
– by thermal imaging 213
– by X-ray methods, 22, 55, 87, 93, 251, 260, 271, 333, 357, 369, 378, 495, 505, 507, 515, 524, 529
– by X-ray photoelectron spectroscopy 271
Clusters 41, 204
Computer simulation 139
Constitutional supercooling 105, 364
Convection 139, 364, 447
Copper
– chloride 378

Dendritic growth 158, 191
Devices 387, 436
Diamond 15, 225
Diffusional control 41, 55, 158, 251, 294, 518
Dislocations 37, 87, 260, 307, 340, 364, 515
Dissolution 421, 473
Distribution coefficient 191, 461, 515
Dopants 15, 75, 151, 169, 191, 369, 436, 461, 518, 521

Etching
– chemical 364, 369, 515

Gadolinium
– molybdate 185
Gallium
– arsenide 48, 98, 169, 213, 240, 351, 369, 387, 461, 511, 518
– indium arsenide 521
Germanium 158
Glycine 421
Gold
– telluride 397
Gypsum 87

Hafnium
– germanate 151
– silicate 151
Heat flow control 127, 139
Heterojunction 436, 521

Impurity 225, 240, 351
Inclusions 63
Indium
– arsenide 81
– gallium antimonide arsenide 204
– gallium arsenide 98, 271, 436
– gallium phosphide 436
– organic 511
– phosphide 75
Interface 63, 81, 98, 139, 158, 235, 271, 294, 364, 397, 511, 515, 518

Kinetics
– of growth 63, 158, 169, 251, 283, 294, 319, 340, 414, 473, 483
– of interface control 158, 294, 414
– of nucleation 158, 191, 294, 414, 483, 495
– of transformation 421, 473

Lasers 505
Lead
– tin telluride 139
– titanate 251
Lithium
– iodate 63
– niobate 185, 327
Lysozyme 289, 414

Mathematical model 139
Melt growth technique
– by Bridgman–Stockbarger method
– – of cadmium zinc telluride 515
– – of lead tin telluride 139
– – theory of 139
– by Czochralski method
– – of gadolinium molybdate 185
– – of gallium arsenide 213, 369, 461
– – of lithium niobate 185, 327
– – of tellurium dioxide 364
– – theory of 447
– by floating zone method
– – theory of 22
– by uniaxial solidification
– – of bismuth strontium calcium cuprate 529
– by zone melting
– – of gallium arsenide 369
Microgravity 105, 127, 289
Molybdenum
– carbide 307
Morphological stability 105, 158, 235, 397
Morphology of growth 15, 27, 87, 158, 191, 225, 243, 283, 314, 319, 333, 340, 378, 397, 421, 473, 495, 524

Nucleation 41, 294, 307, 314, 473, 495
Numbers
– Grashof 447
– Nusselt 139
– Peclet 139
– Seeger 158
– Sherwood 158
Numerical analysis 158

Organic crystals 191, 289, 314, 333, 421, 495

Perfection of crystals 22, 55, 63, 75, 81, 87, 93, 158, 225, 260, 369, 515
Phase diagrams 178, 204, 427, 505
Phenomenological theory 294, 397, 473
Polymorphism/polytypism 333, 421
Potassium
– tantalate niobate 27
– yttrium tungstate 505
Precursor 48, 436
Purification of materials 240, 414

Segregation 461
Silicon 22, 178
– germanium 1, 260
Silver 243
Solid growth technique
– by polymorphic transformation
– – of barium fluoride 473
– – of triglycerides 333
– by recrystallization
– – of copper chloride 378
Solubility 427
Solution growth technique
– by flux method
– – of boron nitride 507
– – of diamond 15
– – of hafnium germanate 151
– – of hafnium silicate 151
– – of potassium tantalate niobate 27
– – of potassium yttrium tungstate 505
– – of zirconium germanate 151
– – of zirconium silicate 151
– by hydrothermal growth
– – of aluminum orthophosphate 427
– – of barium hexaferrite 483
– – of lead titanate 251
– by low temperature method
– – of barium nitrate 340
– – of gypsum 87
– – of lithium iodate 63
– – of lysozyme 289
– by solvent evaporation
– – of lysozyme 414
Statistical mechanics, molecular theory 397
Stefan problem or moving boundary problem 158
Step 158, 178

Strain 81, 260, 271
Superconductivity 37, 529
– bulk 37, 529
– characterization 37, 529
– crystal chemistry 529
– high T_c 37, 529
– stoichiometry 529
Supercooling, supersaturation 41, 158, 294, 427, 515
Superlattices 235, 397
Surface energy, determination of 397
Surface processes 158, 283, 397
Surface structure 178, 235, 340, 397

Tellurium
– dioxide 364
Thermodynamics 1, 41, 204
Thin film growth
– by chemical beam epitaxy
– – of indium gallium arsenide 271
– by liquid phase epitaxy
– – of gallium arsenide 240, 351
– – of indium gallium antimonide arsenide 204
– by metalorganic molecular beam epitaxy
– – of gallium arsenide 511
– – of zinc selenide 283
– by molecular beam epitaxy
– – of gallium arsenide 518
– – of indium arsenide 81
– – of organic crystals 495
– – of silicon germanide 260
– – of silver 243
– – of III–V compounds 98, 436
– – of titanium oxides 235
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of gallium arsenide 387
– – – of indium phosphide 75
– – – of silicon germanide 1
– – – of triglycerides 333
– – through evaporation and condensation
– – – of cadmium telluride 55
– – through metalorganic chemical vapor deposition
– – – of gallium arsenide 169, 511
– – – of gallium indium arsenide 521
– – through photochemical stimulation
– – – of gallium arsenide 48
– – – theory of 48
– – by sputtering
– – – of zinc oxide 357
Three–five (III–V) compounds 98, 436
Titanium
– oxides 235
Twinning 87

Vapor growth technique
– by combustion flame method
– – of molybdenum carbide 307
– theory of 105
Vapor–liquid–solid growth
– of lysozyme 414

Whisker growth
– of bismuth strontium calcium cuprate 524
– of molybdenum carbide 307

Yttrium
– barium cuprate 37

Zinc
– halides 397
– oxide 357
– selenide 283
Zirconium
– germanate 151
– silicate 151